

TO-3P

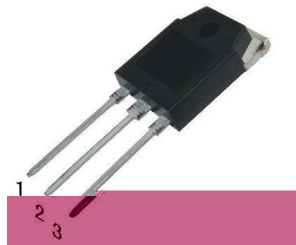
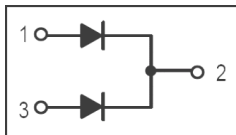
Schottky Barrier Diode in a TO-3P Plastic Package.

Low forward voltage drop, low power losses, High efficiency operation.

OR-ing

DC-DC

For use in high frequency inverters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.



PIN1 Anode PIN 2 Cathode PIN 3 Anode

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RM} V_{RWM} V_{DC}	200	V
RMS Reverse Voltage	V_{RMS}	140	V
Average forward current	$I_{F(AV)}$	2×15	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	200	A
Thermal Resistance Junction to Ambient case	$R_{\theta Jc}$	1.4	$^{\circ}C/W$
Operating and Storage Temperature Range	T_j T_{stg}	-40 +150	$^{\circ}C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V_{BR}	$I_R=1mA(T_a=25^{\circ}C)$	200			V
Forward Voltage	V_F	$I_F=5A(T_a=25^{\circ}C)$		0.73	0.85	V
		$I_F=10A(T_a=25^{\circ}C)$		0.80	0.95	V
		$I_F=15A(T_a=25^{\circ}C)$		0.92	1.15	V
		$I_F=5A(T_a=125^{\circ}C)$		0.58		V
		$I_F=10A(T_a=125^{\circ}C)$		0.66		V
		$I_F=15A(T_a=125^{\circ}C)$		0.71	0.85	V
Instantaneous Reverse current (Note 1)	I_R Note 1	$V_R=200V(T_a=25^{\circ}C)$		4	20	μA
		$V_R=200V(T_a=125^{\circ}C)$		5	10	mA

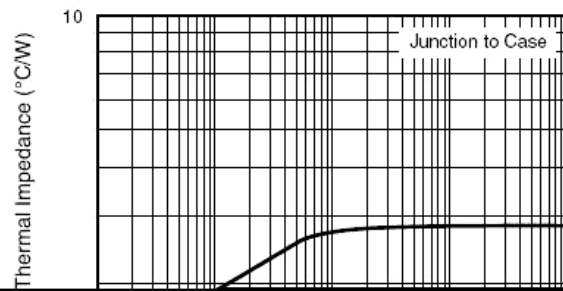
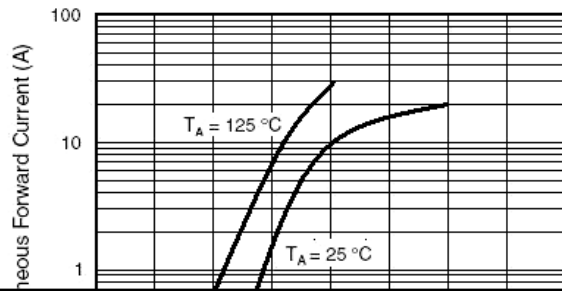
/Notes

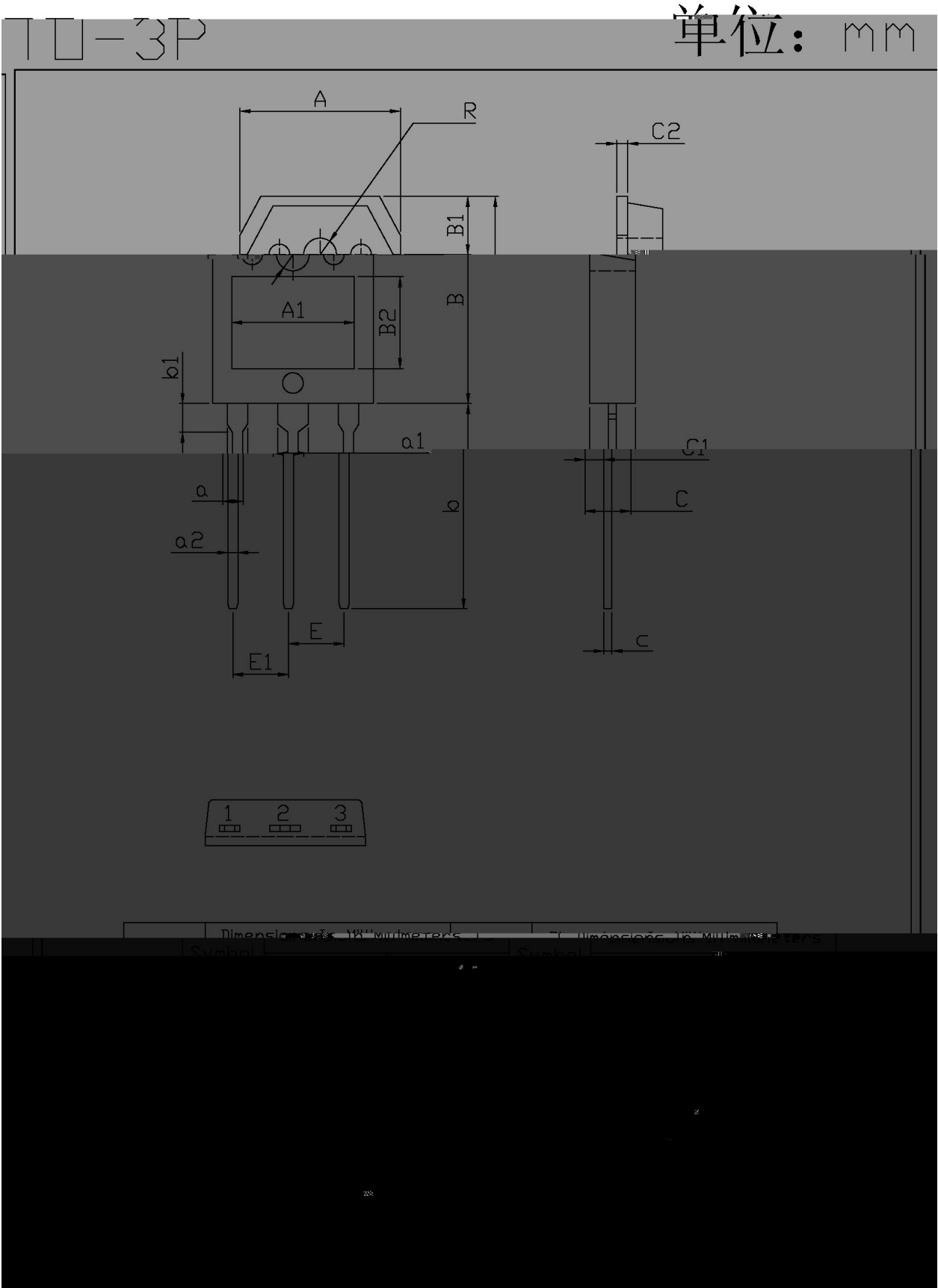
 1.
effect.

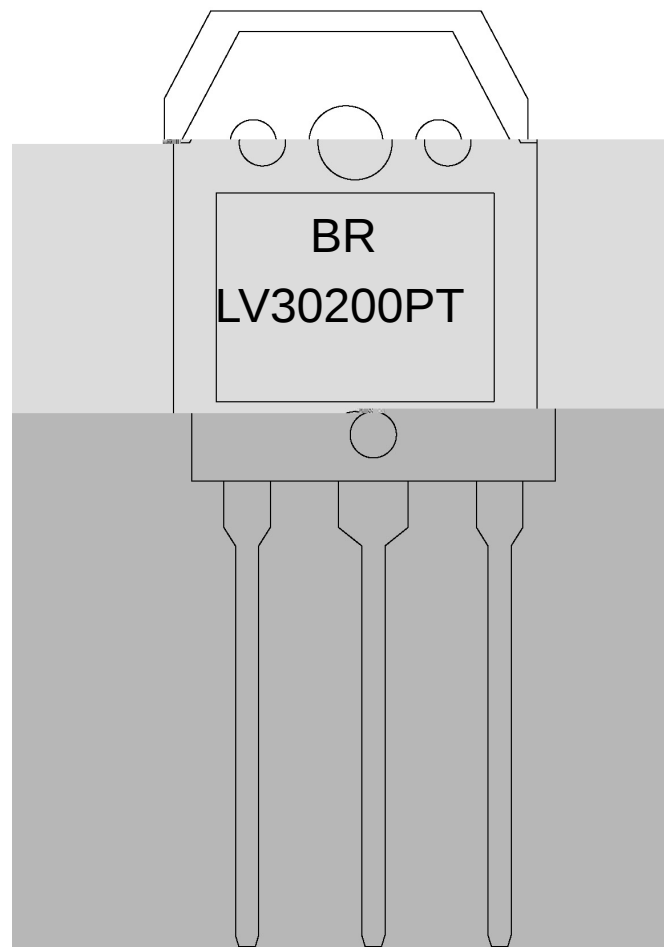
 2.
single chip.

/Short duration pulse test used to minimize self-heating

/ Unless otherwise noted, values for the parameters of a







BR

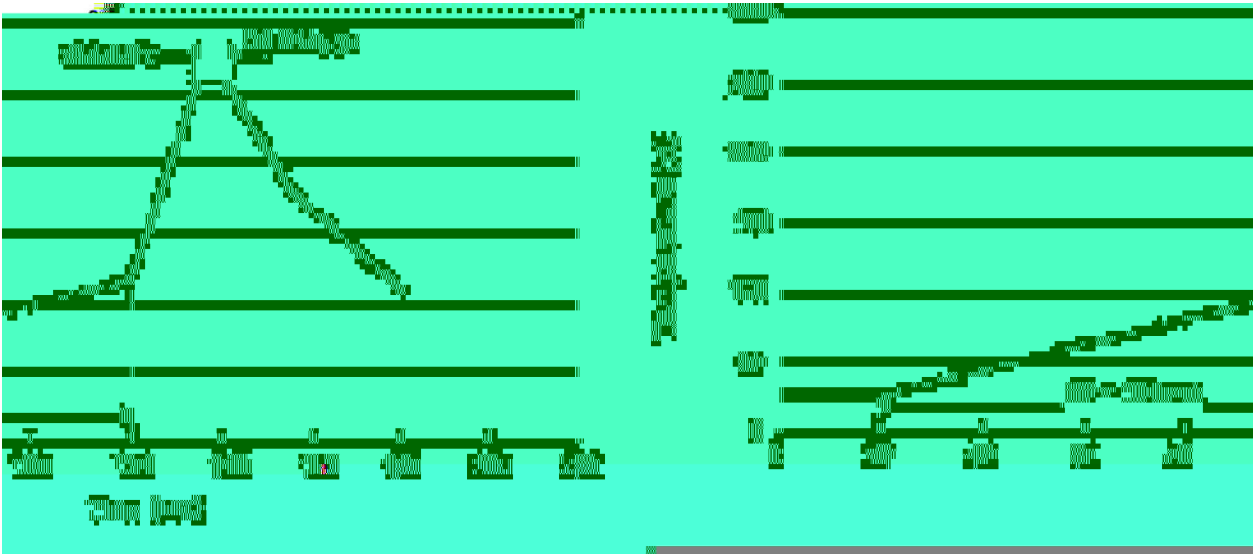
LV30200PT

Note:

BR: Company Code.

LV30200PT: Product Type.

****: Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3

2 10

/sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5℃

Time:10±1 sec

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱
								× ×